

IN THE SPECIFICATION:

Please replace the paragraph at page 18, line 26, to page 19, line 4 with the following amended paragraph:

In each sub-pixel, the ~~easing~~ erasing TFT 112 is connected to the erasing gate signal line of the sub-pixel. In this embodiment mode, a gate electrode of the erasing TFT 112 of the first sub-pixel 105 is connected to the first erasing gate signal line GeL_j and a gate electrode of the erasing TFT 112 of the second sub-pixel 106 is connected to the second erasing gate signal line GeR_j.

Please replace the paragraph at page 38, line 24, to page 39, line 2 with the following amended paragraph:

In each sub-pixel, the ~~easing~~ erasing TFT 312 is connected to the erasing gate signal line of the sub-pixel. In this embodiment, a gate electrode of the erasing TFT 312 of the first sub-pixel 305 is connected to the first erasing gate signal line GeL_j and a gate electrode of the erasing TFT 312 of the second sub-pixel 306 is connected to the second erasing gate signal line GeR_j.

Please replace the paragraph at page 42, lines 2-8 with the following amended paragraph:

In each sub-pixel, the ~~easing~~ erasing TFT 412 is connected to the erasing gate signal line of the sub-pixel. In this embodiment, a gate electrode of the erasing TFT 412 of the first sub-pixel 405 is connected to the first erasing gate signal line GeL_j, a gate electrode of the erasing TFT 412 of the second sub-pixel 406 is connected to the second erasing gate signal line GeR_j, and a gate electrode of the erasing TFT 412 of the third sub-pixel 407 is connected to the third erasing gate signal line GeT_j.

Please replace the paragraph at page 55, lines 15-24 with the following amended paragraph:

Thereafter, a resist mask having a predetermined pattern is formed to form contact holes that reach the respective impurity regions formed in the semiconductor layers so as to function as a source or drain region. These contact holes are formed with a dry etching method. In this case, a mixture gas of CF_4 , O_2 , and He is used as an etching gas to first etch away the second interlayer insulating film 939 made of the organic insulating material. The first interlayer insulating film 937 is then etched away with a mixture gas of CF_4 and O_2 as an etching gas. Furthermore, the etching gas is switched to CHF_3 so as to enhance a selection ratio with respect to the semiconductor layers, and the third shaped gate insulating films ~~570~~ 906 are etched away, thereby resulting in the contact holes being formed.